Two Stage Dual Gate MESFET Monolithic Gain Control Amplifier for Ka-Band

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A monolithic two stage gain control amplifier has been developed using submicron gate length dual gate MESFETs fabricated on ion implanted material. The amplifier has a gain of 12 dB at 30 GHz with a gain control range of over 30 dB. This ion implanted monolithic IC is readily integrable with other phased array receiver functions such as low noise amplifiers and phase shifters.

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